
2SD2342

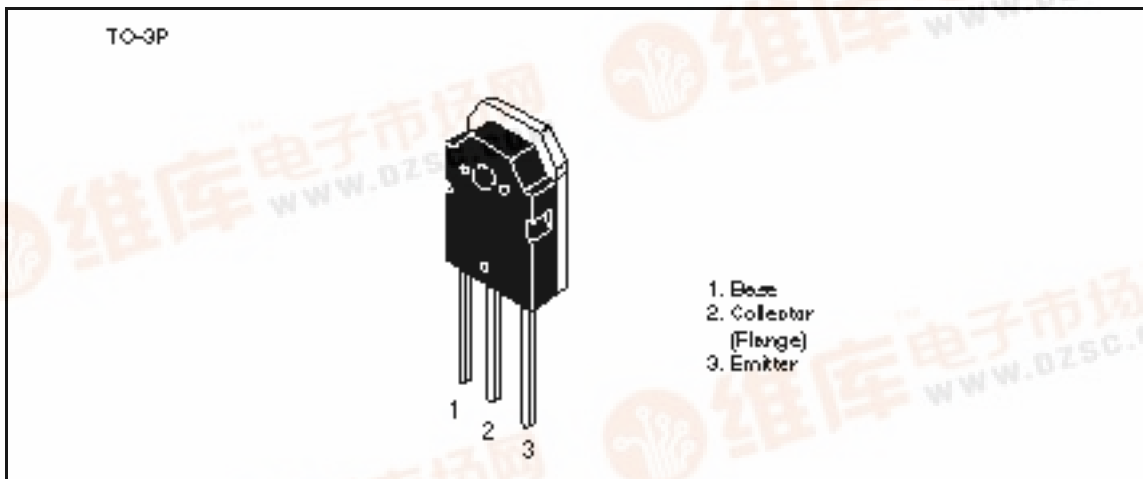
Silicon NPN Triple Diffused

HITACHI

Application

Low frequency power amplifier

Outline



2SD2342

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	150	V
Collector to emitter voltage	V_{CEO}	80	V
Emitter to base voltage	V_{EBO}	6	V
Collector current	I_C	6	A
Collector peak current	$I_{C(peak)}$	10	A
Collector power dissipation	P_C^{*1}	50	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-50 to +150	°C

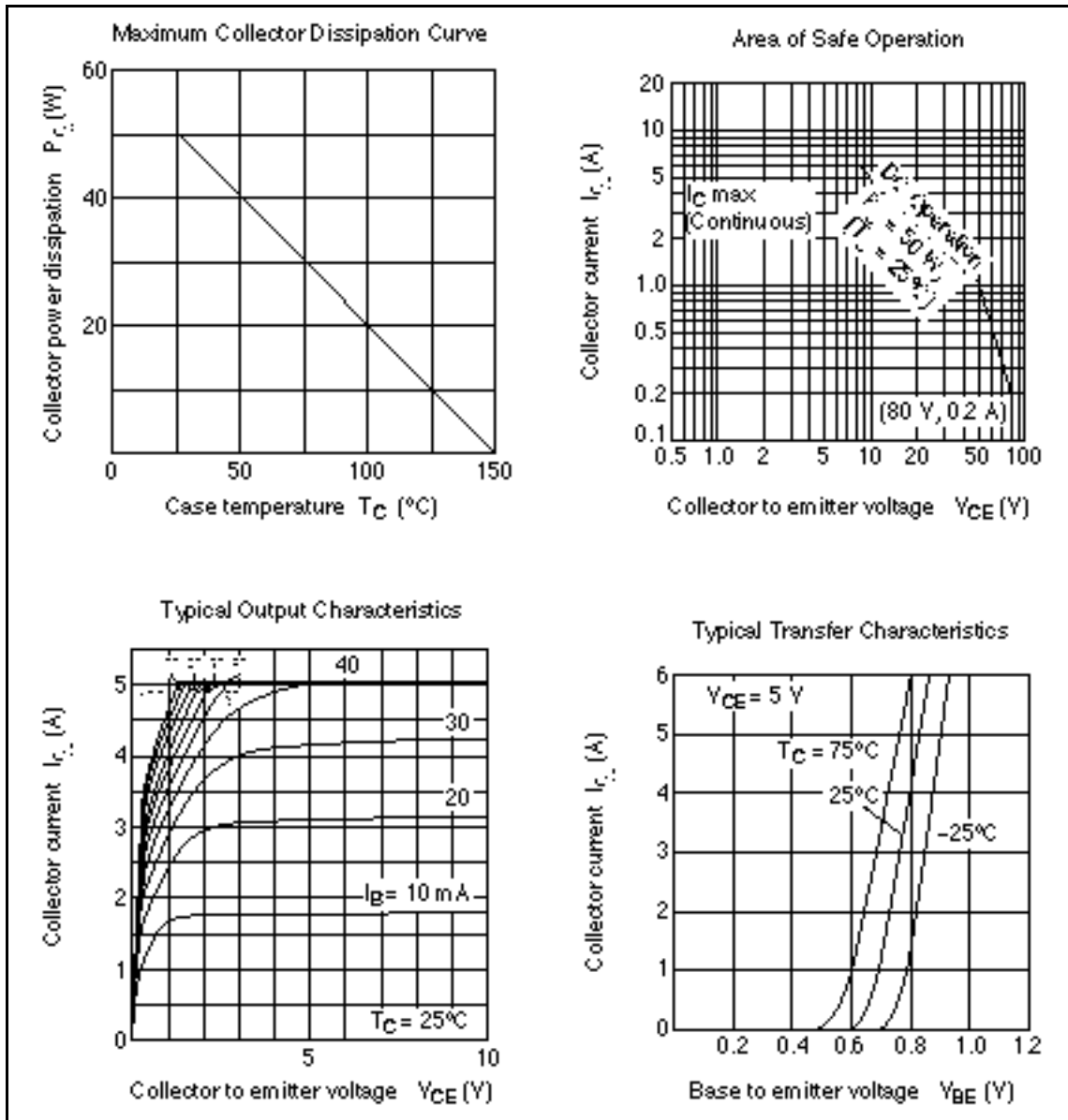
Note: 1. Value at $T_C = 25^\circ\text{C}$.

Electrical Characteristics (Ta = 25°C)

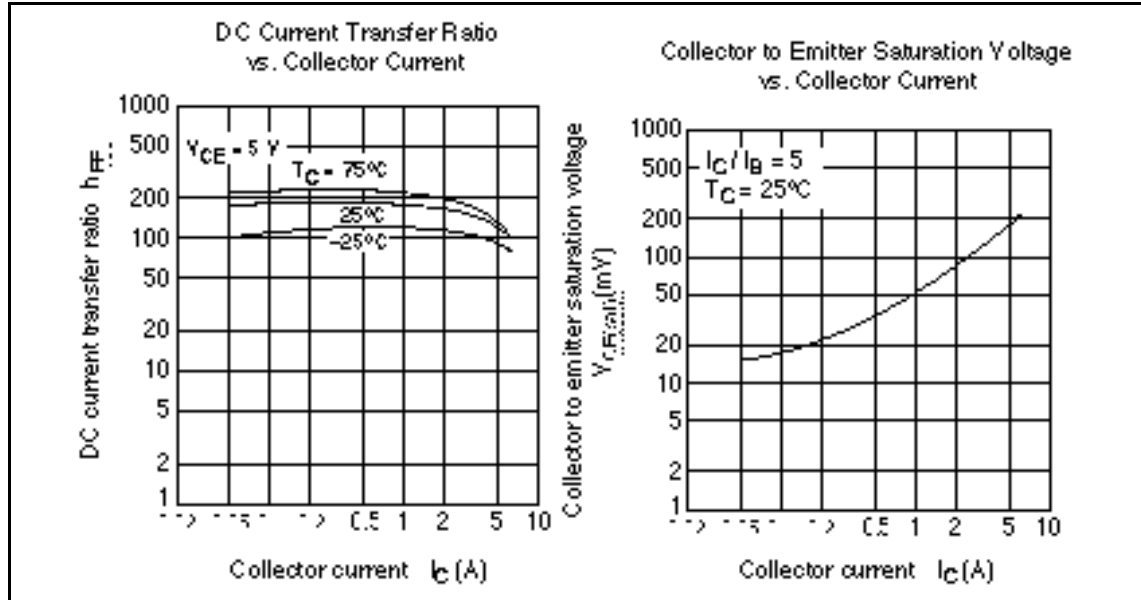
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	150	—	—	V	$I_C = 5\text{ mA}, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	80	—	—	V	$I_C = 50\text{ mA}, R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	6	—	—	V	$I_E = 5\text{ mA}, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	10	μA	$V_{CB} = 120\text{ V}, I_E = 0$
DC current transfer ratio	h_{FE1}^{*1}	60	—	200		$V_{CE} = 5\text{ V}, I_C = 1\text{ A}$
	h_{FE2}	22	—	—		$V_{CE} = 5\text{ V}, I_C = 5\text{ A}$
Base to emitter voltage	V_{BE}	—	—	1.0	V	$V_{CE} = 5\text{ V}, I_C = 1\text{ A}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	1.5	V	$I_C = 5\text{ A}, I_B = 1\text{ A}$

Note: 1. The 2SD2342 is grouped by h_{FE1} as follows.

B	C
60 to 120	100 to 200



2SD2342



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